

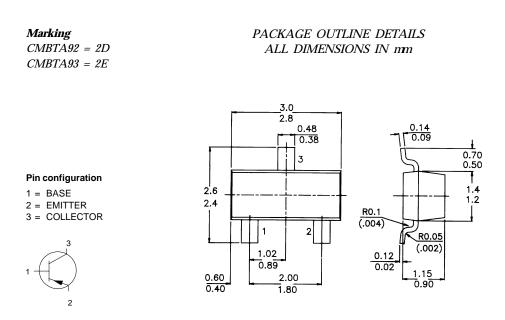


SOT-23 Formed SMD Package

CMBTA92 CMBTA93

SILICON EPITAXIAL TRANSISTORS

P-N-P transistor



CNADT A 09

A93 200 V 200 V

V

mА

mW

MHz

8 pF

5

500

250

40

50

ABSOLUTE MAXIMUM RATINGS

		CIVIDI	AYZ
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	300
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	300
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	
Collector current (d.c.)	$-I_C$	max.	
Total power dissipation up to $T_{amb} = 25 \ ^{\circ}C$	P _{tot}		
D.C. current gain			
$-I_C = 10 \text{ mA; } -V_{CE} = 10 \text{ V}$	h _{FE}	min.	
Transition frequency at $f = 100 \text{ MHz}$			
$-I_C = 10 \text{ mA; } -V_{CE} = 20 \text{ V}$	f_T	min.	
Collector-base capacitance at $f = 1 MHz$			
$I_E = 0; -V_{CB} = 20 V$	C _{cb}	max.	6

CMBTA92 CMBTA93

RATINGS (at $T_A = 25^{\circ}C$ unless otherwise specified) Limiting values

Linning values				
		CMBTA 92	? A9.	3
Collector-base voltage (open emitter)	$-V_{CBO}$	max. 300	200	$\bar{O} V$
Collector-emitter voltage (open base)	$-V_{CEO}$	max. 300	200	9 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	500	mА
Total power dissipation up to $T_{amb} = 25 \ ^{\circ}C$	P _{tot}	max	250	mW
Storage temperature	T _{stg}	-	–55 to +150	° C
Junction temperature	Τj	max.	150	° C

THERMAL CHARACTERISTICS

$T_j = P (R_{th j-t} + R_{th t-s} + R_{th s-a}) + T_{th s-a}$	amb		
Thermal resistance			
from junction to ambient	R _{th j-a}	500	K/W

CHARACTERISTICS (at $T_A = 25^{\circ}C$ unless otherwise specified) Collector-amitter breakdown voltage

Collector-emitter breakdown voltage						
$-I_C = 1 mA; I_B = 0$	$-V_{(BR)CE}$	у min.	300		200	V
Collector-base breakdown voltage						
$-I_C = 100 \ \mu A; I_E = 0$	-V(BR)CBC	у <i>тіп.</i>	300		200	V
Collector cut-off current						
$-V_{CB} = 200 \ V; \ I_E = 0$	$-I_{CBO}$	max.	0.25		-	μA
$-V_{CB} = 160 V; I_E = 0$	-ICBO	max.	-		0.25	μA
Emitter-base breakdown voltage						
$-I_E = 100 \ \mu A; \ I_C = 0$	$-V_{(BR)EBO}$	у <i>тіп.</i>		5		V
Emitter cut-off current						
$I_C = 0; -V_{BE} = 3 V;$	$-I_{EBO}$	max.	0.1		0.1	${\tt m}A$
Collector-base capacitance at f= 1 MHz						
$I_E = 0; -V_{CB} = 20 V$	C_{cb}	max.	6		8	рF
Saturation voltages						
$-I_C = 20 mA; -I_B = 2 mA$	-V _{CEsat}	max.	0.5		0.5	V
$-I_C = 20 \ mA; \ -I_B = 2 \ mA$	-VBEsat	max.	0.9		0.9	V
D.C. current gain						
$-I_C = 1 mA; -V_{CE} = 10 V$	h_{FE}	min.		25		
$-I_C = 10 \text{ mA}; -V_{CE} = 10 \text{ V}$	h_{FE}	min.		40		
$-I_C = 30 \text{ mA}; -V_{CE} = 10 \text{ V}$	h _{FE}	min.		25		

Customer Notes

Disclaimer

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Data Sheet